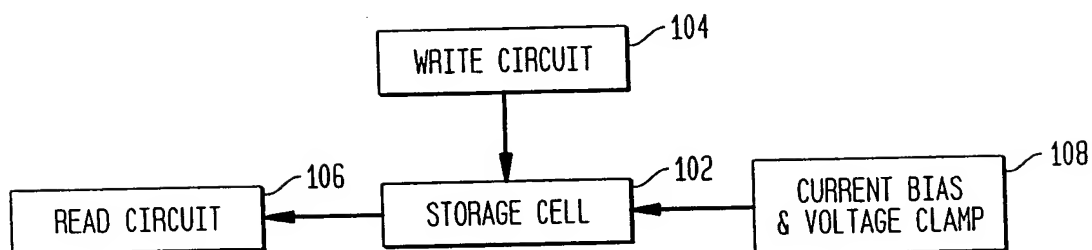
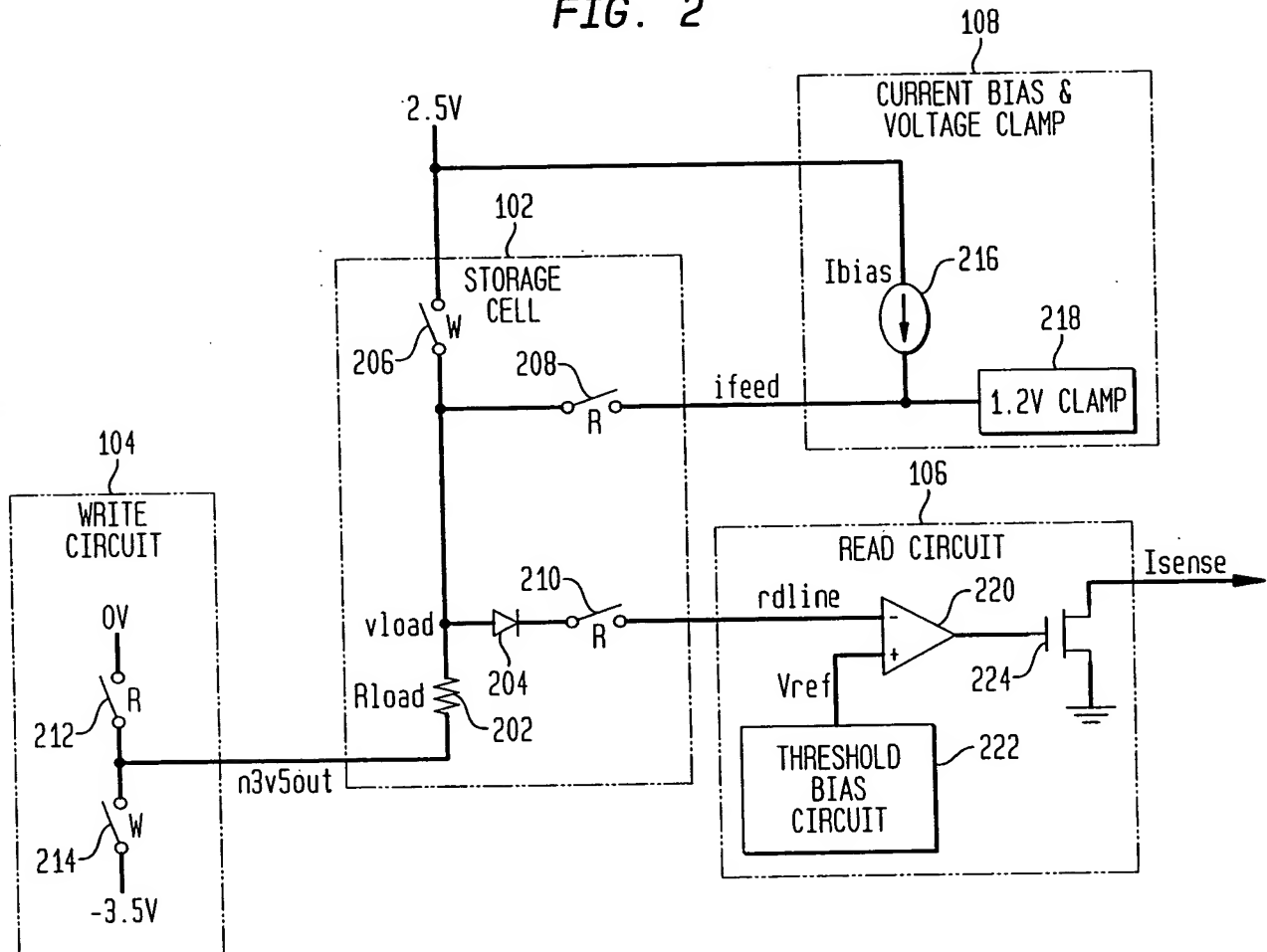


FIG. 1



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 Title: System and Method for One-time Programmed  
 Memory Through Direct-Tunneling Oxide Breakdown

FIG. 2



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FIG. 3

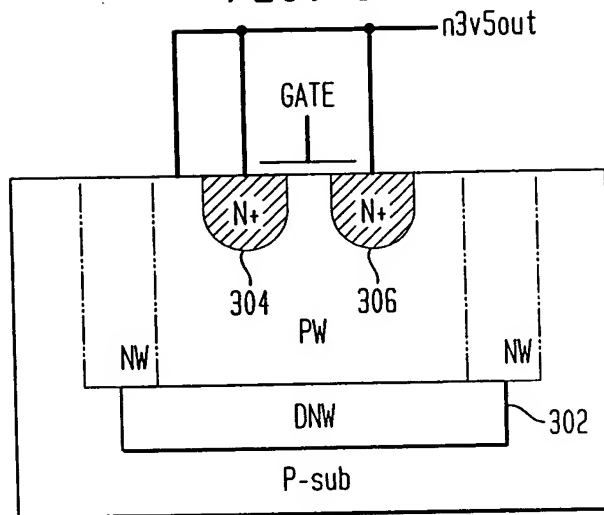
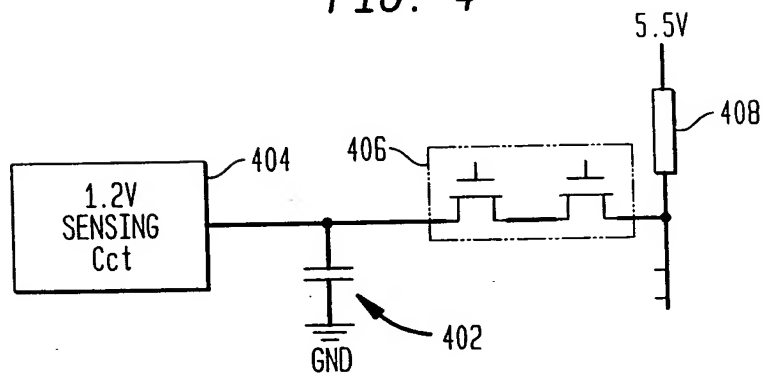
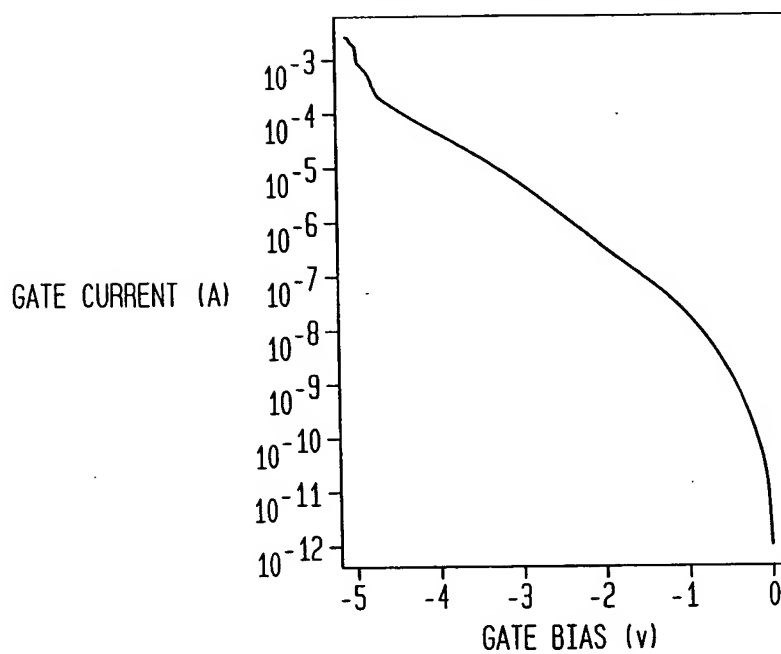
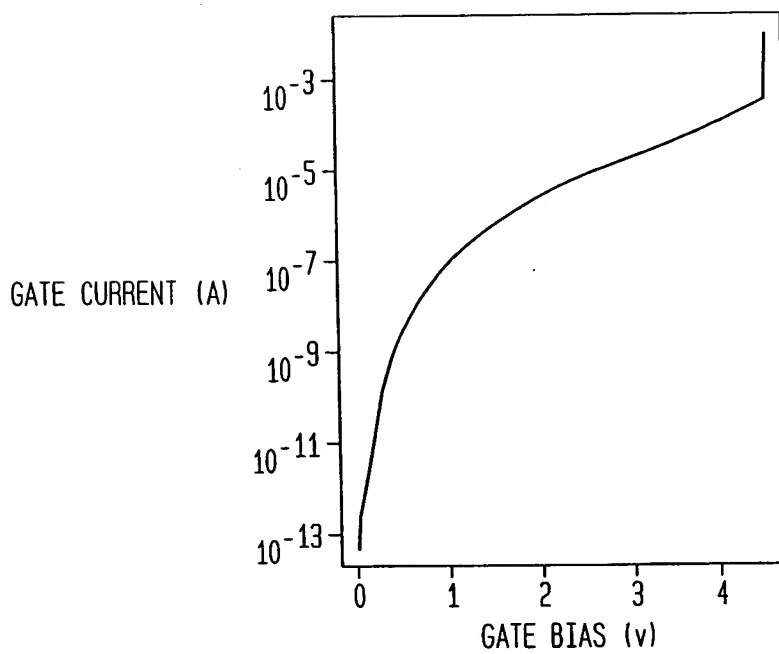


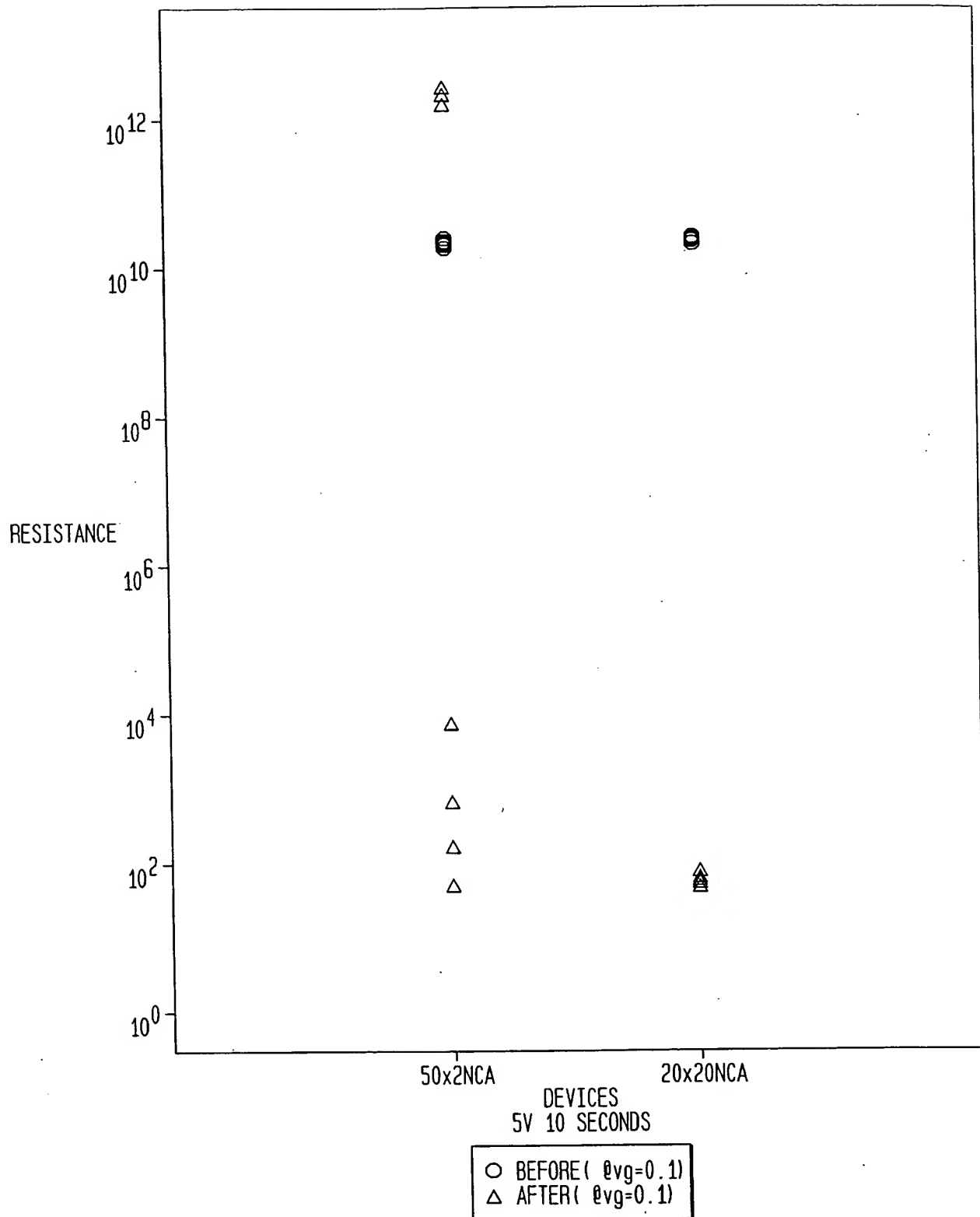
FIG. 4



**FIG. 5A**NMOS FET  $10 \times 10 \text{ } \mu\text{m}^2$  S/D FLOAT.**FIG. 5B**NMOS FET  $10 \times 10 \text{ } \mu\text{m}^2$ 

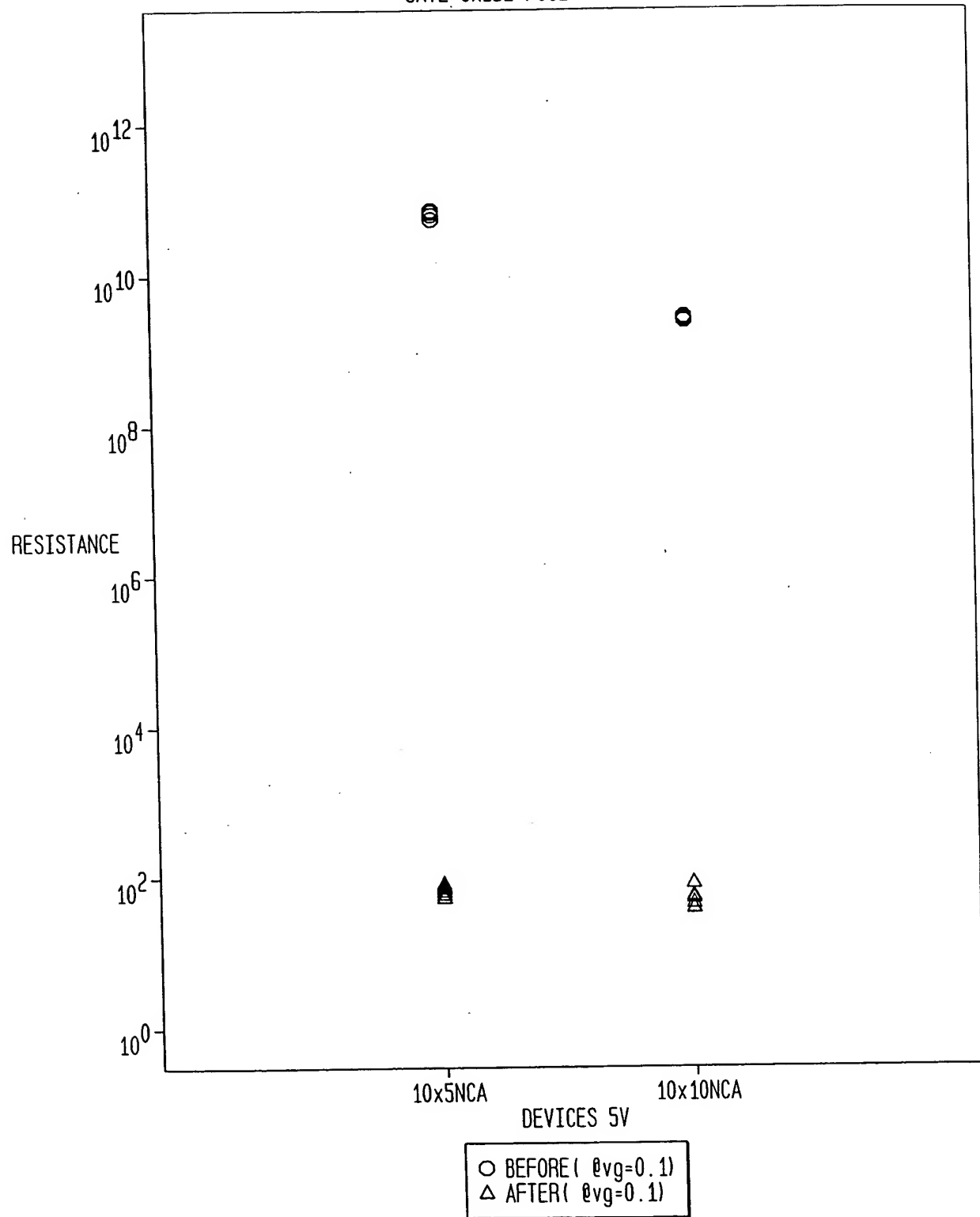
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**FIG. 6A**  
GATE OXIDE FUSE



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**FIG. 6B**  
GATE OXIDE FUSE



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FIG. 7

